

Application No. 10/736,709
Amendment dated August 13, 2008
Reply to Office Action of April 14, 2008

Docket No.: 0630-1835P

AMENDMENTS TO THE CLAIMS**RECEIVED
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Please amend the claims as follows:

1. (Currently Amended) A method for forming a pattern, comprising:

providing a substrate on which a plurality of unit panels and etching object layers on the respective unit panel areas are formed;

dividing the substrate into first and second at least two areas, each of the first and second two areas having at least one unit panel;

providing a cliché on which a plurality of grooves are formed, the cliché being divided into first and second portions a plurality of areas corresponding to the first and second divided areas of the substrate;

filling resist in the grooves;

transferring the resist in the grooves of the first portion one area of the cliché on a blanket applied on a surface of a printing roll by contacting and rotating the printing roll with the first portion of blanket on the cliché, the printing roll corresponding to the first divided area of the substrate; and

applying the resist transferred on the surface of the blanket of the printing roll on the etching object layer on the first area of the substrate ~~corresponding to the area of the cliché~~;

transferring the resist in the grooves of the second portion of the cliché on a blanket applied on a surface of the printing roll by contacting and rotating the printing roll with the second portion of the cliché, the printing roll corresponding to the second portion of the cliché;
and

applying the resist transferred on the surface of the blanket of the printing roll on the etching object layer on the second area of the substrate.

2. (Currently Amended) The method of claim 1, wherein the printing roll has a same width as that of the divided first and second areas area of the substrate.

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3. (Canceled)

4. (Currently Amended) The method of claim 2, wherein a length of the blanket of the printing roll is the same as a length of a circumference of the printing roll, which is same as a length of the first and second areas ~~divided area~~ of the substrate.

5. (Original) The method of claim 1, wherein the divided area of the substrate includes one or more unit panels.

6. (Cancelled).

7. (Currently Amended) The method of claim 1, wherein the printing roll is formed to have a same size as that of the first and second areas ~~divided area~~ on the substrate.

8. (Original) The method of claim 1, wherein the etching object layer includes a metal layer.

9. (Original) The method of claim 1, wherein the etching object layer includes an insulating layer comprised of SiO_x or SiN_x.

10. (Original) The method of claim 1, wherein the etching object layer is a semiconductor layer.

11. (Currently Amended) A method for forming a pattern, comprising:

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providing a substrate on which a plurality of unit panels and etching object layers on the respective unit panel areas are formed;

dividing the substrate into a plurality of divided areas so as to include at least one or more unit panels;

providing a cliché on which a plurality of grooves are formed, the cliché being divided into a plurality of areas corresponding to the divided areas of the substrate;

filling resist in the grooves of the cliché;

providing a blanket on a printing roll having a same width as that of the divided area of the substrate;

transferring the resist filled in the grooves of one of the divided area-areas of the cliché onto a surface of the blanket on the printing roll by contacting and rotating the printing roll with the ~~blanket on one of the divided area-areas~~ of the cliché corresponding to the divided area of the substrate; and

applying the resist transferred on the surface of the blanket on the etching object layer on the area of the substrate corresponding to the one of the divided area of the cliché;

transferring the resist filled in the groove of another of the divided areas of the cliché onto a surface of the blanket on the printing roll by contacting and rotating the printing roll with the another of the divided areas of the cliché corresponding to another of the divided areas of the substrate; and

applying the resist transferred on the surface of the blanket on the etching object layer on the area of the substrate corresponding to the another of the divided areas of the cliché.

12. (Previously Presented) The method of claim 11, wherein applying the resist on the etching object layer is performed by contacting the resist transferred on the surface of the blanket on the printing roll on the substrate and by rotating the printing roll with the blanket.

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13. (Original) The method of claim 11, wherein the divided area of the substrate includes at least one unit panel.

14. (Original) The method of claim 11, wherein the etching object layer includes a metal layer.

15. (Original) The method of claim 11, wherein the etching object layer comprises an insulating layer comprised of SiOx or SiNx.

16. (Original) The method of claim 11, wherein the etching object layer is a semiconductor layer.

17-27. (Canceled)

28. (Previously Presented) The method of claim 1, wherein the blanket improves adhesive force with the resist.

29. (Previously Presented) The method of claim 11, wherein the blanket improves adhesive force with the resist.

30-32. (Canceled)